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AMENDMENT TO CLAIMS

Claims 1, 12, and 18-21 are currently amended.

Claims 7, 8, have been previously amended.

Claims 2-6 and 9 are original.

Claim 23 is added.

Claims 10-11, 13-17 and 22 are cancelled.

1. (Currently amended) A magnetic tunnel junction ~~memory device~~ comprising:
a data layer having a magnetization that can be oriented in first and second
directions; ~~and~~
an unpinned synthetic ferrimagnet reference layer; and
an insulating tunnel barrier between the data layer and the reference layer.
2. (Original) The device of claim 1, wherein the data layer has a higher coercivity
than the reference layer.
3. (Original) The device of claim 1, wherein the reference layer includes first and
second ferromagnetic layers separated by a spacer layer, the first and second
ferromagnetic layers having different coercivities.
4. (Original) The device of claim 3, wherein the spacer layer is electrically
conductive and magnetically non-conductive.
5. (Original) The device of claim 3, wherein the coërcivity of the reference layer is
determined by the ratio of thickness of the first and second ferromagnetic
layers.

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6. (Original) The device of claim 3, wherein magnetic moments of the first and second ferromagnetic layers substantially cancel out.
7. (Previously amended) A magnetic memory device comprising:
a data layer having a magnetization that can be oriented in first and second directions;
a synthetic ferrimagnet reference layer, the data and reference layers having different coercivities;
a first conductor on the reference layer;
an electrical insulator on the first conductor; and
a second conductor on the insulator.
8. (Previously amended) The device of claim 7, further comprising a third conductor in contact with the data layer, the third conductor being orthogonal to the first conductor.
9. (Original) The device of claim 1, further comprising a first conductor in contact with the data layer, and a second conductor in contact with the reference layer, the first and second conductors being orthogonal.

Claims 10-11 (Cancelled)

12. (Previously amended) The device of claim 1, further comprising a ferromagnetic cladding for the reference layer.

Claims 13-17 (Cancelled)

- 2 18. (Currently amended) An information storage device comprising an array of memory cells, each memory cell including at least one magnetic tunnel junction.

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cont.
each magnetic tunnel junction including a data layer and a soft ferrimagnet reference layer, the data and reference layers having magnetizations that can be switched between first and second directions during write operations, only the reference layer being switchable between first and second directions during read operations.

19. (Currently amended) The device of claim 18, wherein each reference layer includes first and second ferromagnetic layers separated by an further comprising electrically conductive and magnetically non-conductive spacers layers separating the data and reference layers.
20. (Currently amended) The device of claim ~~18~~19, wherein reference layer coercivity is determined by the ratio of first ferromagnetic layer thickness to second ferromagnetic layer thickness.
21. (Currently amended) The device of claim ~~18~~19, wherein magnetic moments of the first and second ferromagnetic data and reference layers of a ferrimagnet reference layer substantially cancel out.
22. (Cancelled)
23. (Added) The device of claim 18, further comprising pluralities of word and bit lines for the array of memory cells; and a plurality of read lines for the memory cells.
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